VS-6DKH02-M3

Vishay Semiconductors



www.vishay.com

Hyperfast Rectifier, 2 x 3 A FRED Pt®



1, 2 • 7, 8 3, 4 • 5, 6

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _{F(AV)}	2 x 3 A					
V _R	200 V					
V _F at I _F	0.71 V					
t _{rr}	25 ns					
T _J max.	175 °C					
Package	FlatPAK 5 x 6					
Circuit configuration	Separated cathode					

FEATURES

- Hyper fast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Low forward voltage drop
- Low leakage current
- Specific for output and snubber operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^{\circ}\mathrm{C}$
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002, meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		V _{RRM}		200				
Average rectified forward current	per device		T _{Solderpad} = 170 °C, DC	3	V			
Average rectilied forward current	per device	IF(AV)	$T_{Solderpad} = 169 \ ^{\circ}C, D = 0.5$	3				
Non-repetitive peak surge current -	per device	I _{FSM}	T_J = 25 °C, 10 ms sinusoidal pulse	147	Δ			
Non-repetitive peak surge current -	per diode			70	А			

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)								
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UN								
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-			
Forward voltage	VF	I _F = 3 A	-	0.88	0.94	V		
Forward voltage	VF	I _F = 3 A, T _J = 150 °C	-	0.71	0.74]		
Reverse leakage current	1	$V_{R} = V_{R}$ rated	-	-	2			
neverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	6	40 μA			
Junction capacitance	CT	V _R = 200 V	-	14	-	pF		

Revision: 19-Mar-2021

Document Number: 96082

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

RoHS





Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50$	0 A/µs, V _R = 30 V	-	26	-			
Reverse recovery time	+	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	15	-	ns		
		T _J = 125 °C	I _F = 3 A dI _F /dt = 200 A/μs V _B = 160 V	-	25	-			
Deak receivery ourrent	1	T _J = 25 °C		-	2	-	^		
Peak recovery current	IRRM	T _J = 125 °C		-	3	-	A		
	0	T _J = 25 °C		-	12	-	nC		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	40	-	nc		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C			
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾⁽²⁾		-	90	103				
Thermal resistance, junction to mount	R _{thJM} ⁽³⁾		-	2.3	2.6	°C/W			

Notes

 $^{(1)}$ The heat generated must be less than thermal conductivity from junction to ambient; $dP_D/dT_J < 1 \times R_{thJA}$

 $^{(2)}\,$ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} - junction to ambient

⁽³⁾ Mounted on infinite heatsink

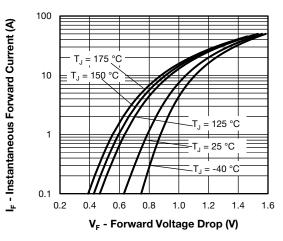


Fig. 1 - Typical Forward Voltage Drop Characteristics

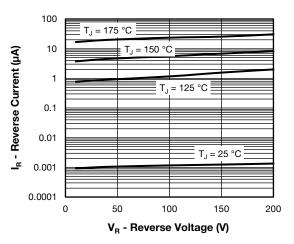


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

2

VS-6DKH02-M3

Vishay Semiconductors

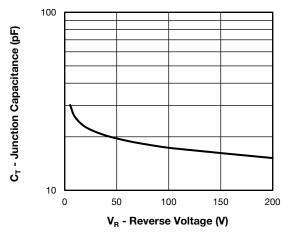


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

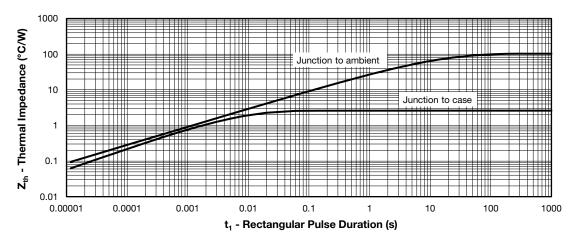


Fig. 4 - Maximum Thermal Impedance Zth Characteristics

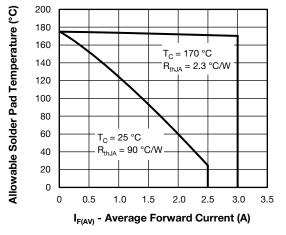


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

Note

4.0 3.5 RMS limit Average Power Loss (W) 3.0 2.5 2.0 D = 0.01 D = 0.05 1.5 D = 0.1 D = 0.2 1.0 D = 0.5 DC 0.5 0 0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 I_{F(AV)} - Average Forward Current (A) Fig. 6 - Forward Power Loss Characteristics

Document Number: 96082

Revision: 19-Mar-2021

SHAY

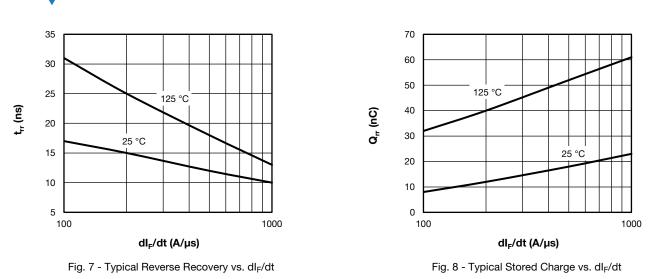
www.vishay.com

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

3



Vishay Semiconductors



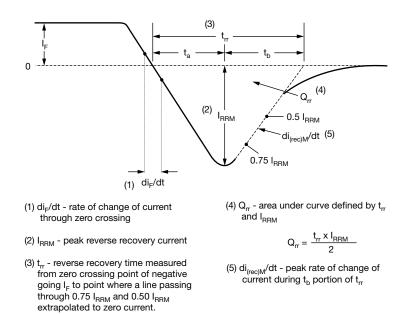


Fig. 9 - Reverse Recovery Waveform and Definitions

Revision: 19-Mar-2021

ISHAY.

www.vishay.com

Document Number: 96082

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

4

VS-6DKH02-M3

Vishay Semiconductors

www.vishay.com

ORDERING INFORMATION TABLE

Device

VISHAY

code	vs-	6	D	к	н	02	-M3
					(5)		
	(1)	(2)	(3)	(4)	()	(6)	(7)
	1	- Vis	hay Sen	niconduc	ctors pro	oduct	
	2	- Cur	rent rati	ng (6 = 0	6 A)		
	3	- Ciro	cuit conf	guratior	ו:		
		D =	separat	ed cath	ode		
	4	- K=	FlatPA	K packa	ge		
	5	- Pro	cess typ	e:			
			hyperfa				
	6	- Vol	tage coo	le (02 =	200 V)		
	7	M3	3 = halog	jen-free	, RoHS-	complia	ant, and

ORDERING INFORMATION (Example)								
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-6DKH02-M3/H	0.10	н	1500	7"diameter plastic tape and reel				
VS-6DKH02-M3/I	0.10	I	6000	13"diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS							
Dimensions www.vishay.com/doc?96056							
Part marking information	www.vishay.com/doc?96059						
Packaging information	www.vishay.com/doc?88869						
SPICE model	www.vishay.com/doc?96882						

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

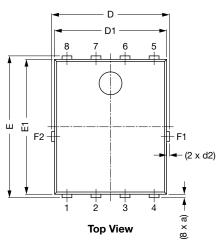


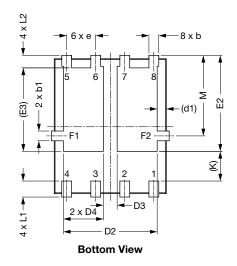
Outline Dimensions

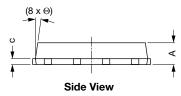
Vishay Semiconductors

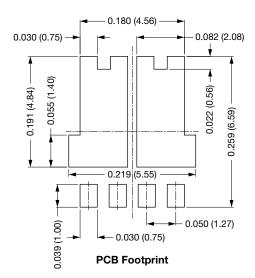
FlatPAK 5 x 6 (Dual)

DIMENSIONS in inches (millimeters)









DIM.		INCHES		MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
А	0.035	0.039	0.043	0.89	0.99	1.09		
(a)	-	0.006	-	-	0.15	-		
b	0.013	0.017	0.020	0.32	0.43	0.52		
b1	0.013	0.017	0.020	0.32	0.43	0.52		
С	0.008	-	0.014	0.20	-	0.35		
D	0.197	0.203	0.209	5.00	5.15	5.30		
D1	0.189	0.193	0.197	4.80	4.90	5.00		
D2	0.154	0.161	0.169	3.90	4.10	4.30		
D3	0.020	0.024	0.031	0.50	0.60	0.80		
D4	0.063	0.069	0.075	1.60	1.75	1.90		
(d1)	-	0.016	-	-	0.40	-		
(d2)	-	0.005	-	-	0.125	-		
E	0.238	0.244	0.250	6.05	6.20	6.35		

Revision: 27-Mar-18

1

Document Number: 96056

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Outline Dimensions

www.vishay.com

Vishay Semiconductors

DIM.		INCHES		MILLIMETERS				
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
E1	0.228	0.232	0.236	5.80	5.90	6.00		
E2	0.157	0.165	0.173	4.00	4.20	4.40		
(E3)	-	0.144	-	-	3.65	-		
е		0.050 BSC			1.27 BSC			
(K)	0.039	-	-	1.00	-	-		
L1	0.019	-	0.043	0.48	-	1.10		
L2	0.012	-	0.031	0.30	-	0.80		
М	0.128	0.138	0.148	3.25	3.50	3.75		
Θ	0°	-	10°	0°	-	10°		

Notes

• Dimensioning and tolerancing per ASME Y14.5-2009

• Dimensions D1 and E1 do not include mold flash or gate burrs

• Dimension (XX) means reference only





www.vishay.com

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.